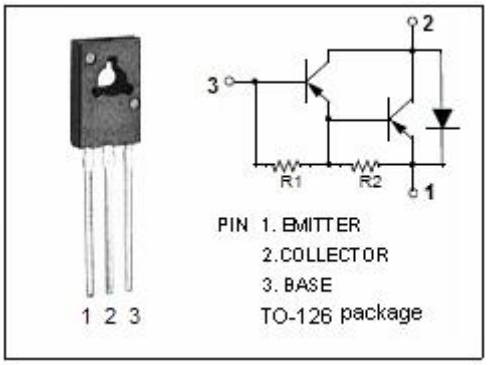
isc Silicon PNP Darlington Power Transistor 2SB786

DESCRIPTION

- Collector-Emitter Sustaining Voltage-
  : $V_{CEO(SUS)}$= -40V(Min)
- High DC Current Gain-
  : h_{FE}= 1000(Min)@ (V_{CE}= -3V, I_C= -0.5A)
- Minimum Lot-to-Lot variations for robust device performance and reliable operation



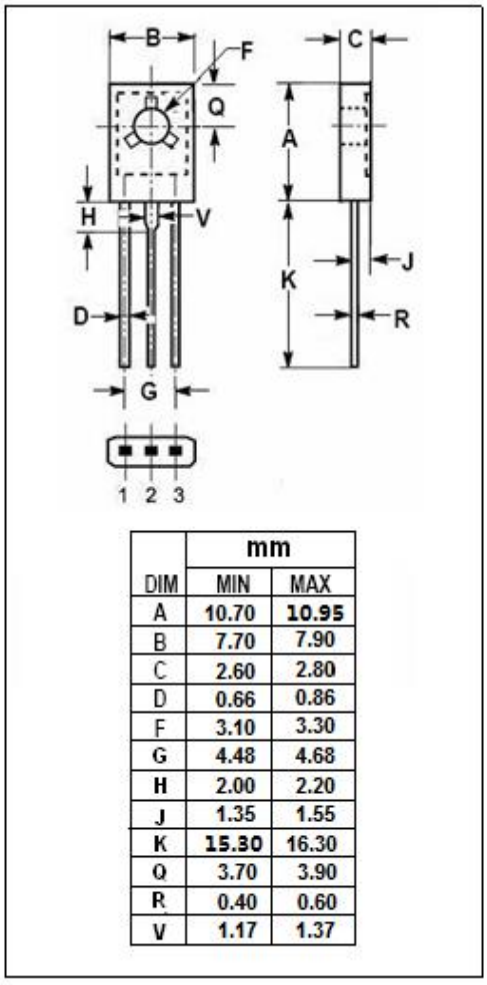
APPLICATIONS

- Designed for general-purpose amplifier and low-speed switching applications.

ABSOLUTE MAXIMUM RATINGS(T_a=25℃)

SYMBOL	PARAMETER	VALUE	UNIT
V_{CBO}	Collector-Base Voltage	-40	V
V_{CEO}	Collector-Emitter Voltage	-40	V
V_{EBO}	Emitter-Base Voltage	-5	V
I_C	Collector Current-Continuous	-2	A
I_{CM}	Collector Current-Peak	-3	A
I_B	Base Current	-0.1	A
P_C	Collector Power Dissipation T_C=25℃	5	W
T_j	Junction Temperature	150	℃
T_{stg}	Storage Temperature Range	-55~150	℃

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DIM	mm MIN	MAX
A	10.70	10.95
B	7.70	7.90
C	2.60	2.80
D	0.66	0.86
F	3.10	3.30
G	4.48	4.68
H	2.00	2.20
J	1.35	1.55
K	15.30	16.30
Q	3.70	3.90
R	0.40	0.60
V	1.17	1.37

isc Silicon PNP Darlington Power Transistor 2SB786

ELECTRICAL CHARACTERISTICS

Tj=25℃ unless otherwise specified

SYMBOL	PARAMETER	CONDITIONS	MIN	TYP	MAX	UNIT
$V_{CEO(SUS)}$	Collector-Emitter Sustaining Voltage	I_C= -10mA; I_B= 0	-40			V
$V_{(BR)EBO}$	Emitter-Base Breakdown Voltage	I_E= -2mA; I_C= 0	-5			V
$V_{(BR)CBO}$	Collector-Base breakdown voltage	I_C=-1mA; I_E= 0	-40			V
$V_{CE(sat)}$	Collector-Emitter Saturation Voltage	I_C= -0.6A; I_B= -1.2mA			-1.5	V
I_{CEO}	Collector Cutoff Current	V_{CE}= -40V; I_B= 0			-0.1	mA
I_{CBO}	Collector Cutoff Current	V_{CB}= -40V; I_E= 0			-1.0	uA
I_{EBO}	Emitter Cutoff Current	V_{EB}= -5V; I_C= 0			-2.0	mA
h_{FE}	DC Current Gain	I_C= -0.5A ; V_{CE}= -3V	1000			
f_T	Current-Gain—Bandwidth Product	I_C=-0.1A ; V_{CE}= -6V		150		MHz
C_{OB}	Output Capacitance	I_E=0; V_{CB}= -10V; f= 1MHz	11			pF

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